



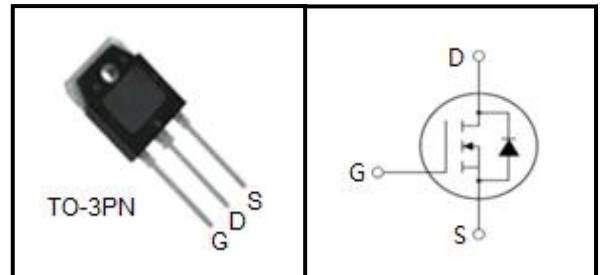
200V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
TMV50N20H	TO-3P	A50N20H



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	200	V
Continuous Drain Current	I_D	50	A
Pulsed Drain Current (note1)	I_{DM}	200	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	1100	mJ
Avalanche Current (note1)	I_{AR}	25	A
Repetitive Avalanche Energy (note1)	E_{AR}	16	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	250	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 25A$	--	40	50	m Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	3950	--	pF
Output Capacitance	C_{oss}		--	550	--	
Reverse Transfer Capacitance	C_{rss}		--	220	--	
Total Gate Charge	Q_g	$V_{DD} = 160V, I_D = 50A,$ $V_{GS} = 10V$	--	135	--	nC
Gate-Source Charge	Q_{gs}		--	16	--	
Gate-Drain Charge	Q_{gd}		--	55	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 100V, I_D = 50A,$ $R_G = 25\Omega$	--	40	--	ns
Turn-on Rise Time	t_r		--	65	--	
Turn-off Delay Time	$t_{d(off)}$		--	110	--	
Turn-off Fall Time	t_f		--	90	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	50	A
Pulsed Diode Forward Current	I_{SM}		--	--	200	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 50A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 50A,$ $di_F/dt = 100A/\mu s$	--	260	--	ns
Reverse Recovery Charge	Q_{rr}		--	2.2	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 25A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 250\mu s$, Duty Cycle $\leq 1\%$



Figure A: Gate Charge Test Circuit and Waveform

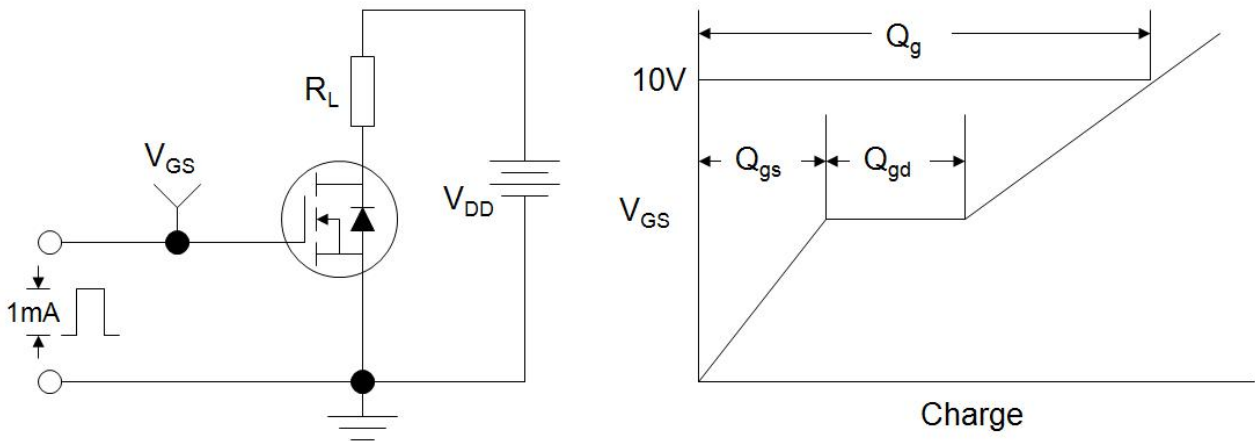


Figure B: Resistive Switching Test Circuit and Waveform

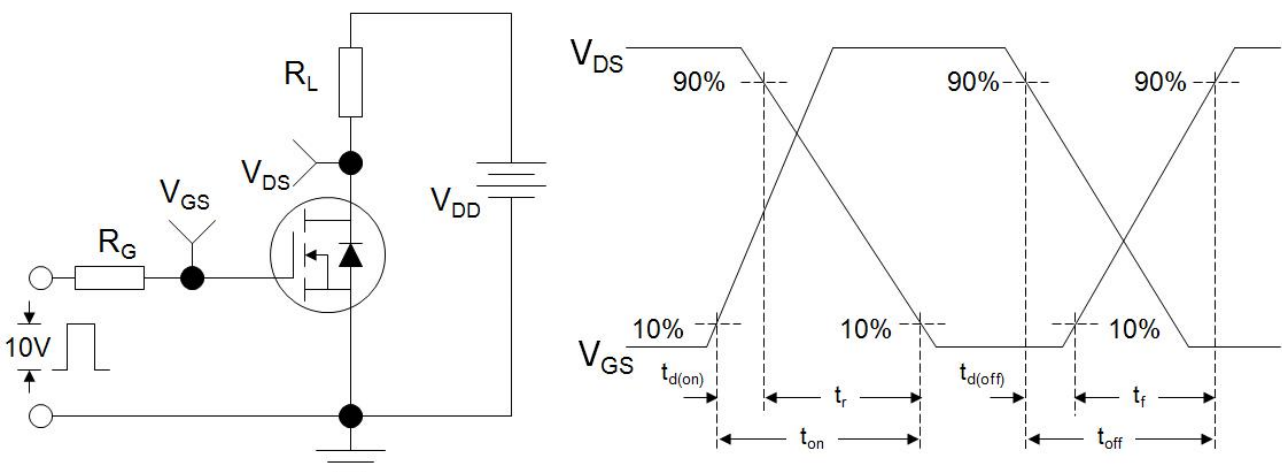
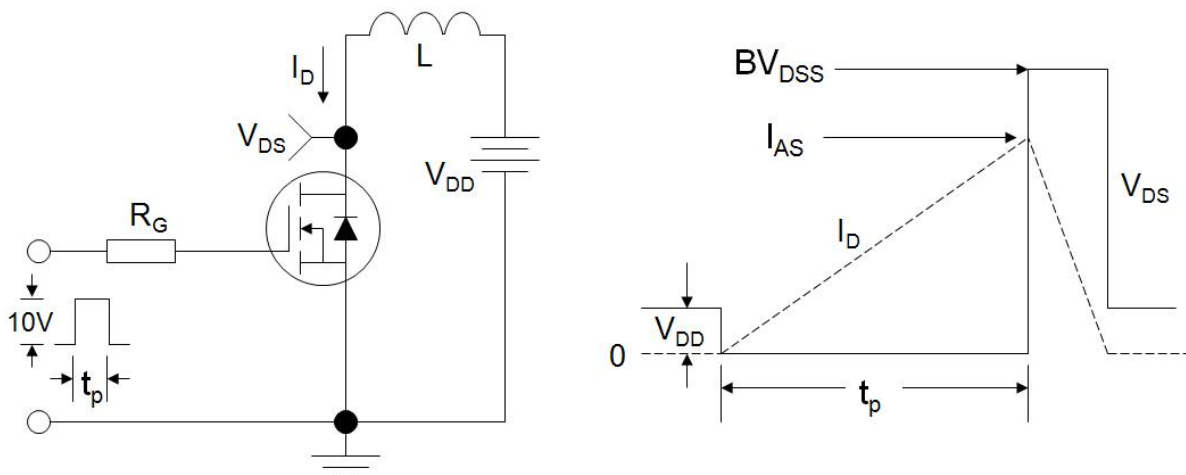
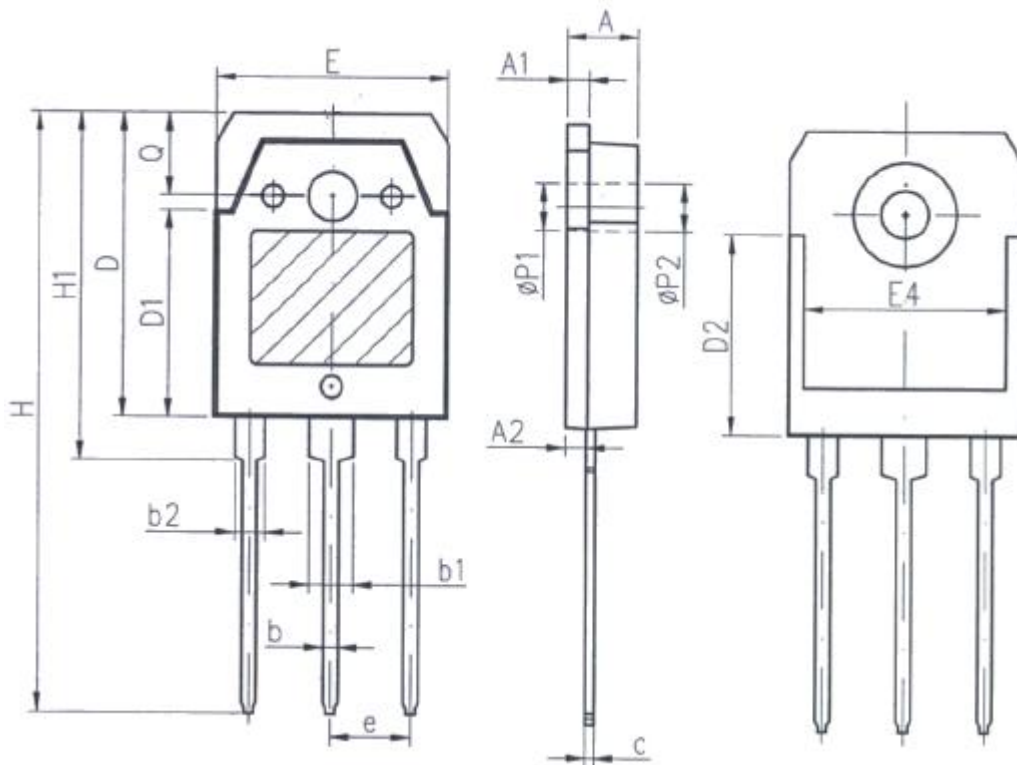


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-3PN



Unit:mm		
Symbol	Min.	Max.
A	4.6	5
A1	1.4	1.65
A2	1.18	1.58
b	0.8	1.2
b1	2.8	3.2
b2	1.8	2.2
c	0.5	0.75
D	19.6	20.2
D1	13.55	14.25
D2	12.9REF	
E	15.35	15.85
E4	12.6	-
e	5.45TYP	
H	40.1	40.9
H1	23.15	23.65
P1	3.2REF	
P2	3.5REF	



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